



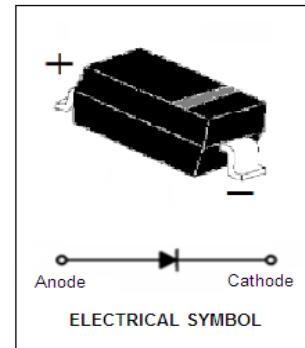
SLS SEMICONDUCTOR (SHENZHEN) CO.,LTD.

SOD-123 封装二极管/SOD-123 Plastic-Encapsulate Diodes**BAV19W/BAV20W/BAV21W (FAST SWITCHING DIODES)****特点/Features :**

Fasting Switching Speed ;
 Surface Mount Package Ideally Suited for
 Automatic Insertion ;
 For General Purpose Switching Applications;
 High Conductance;

印章/ Marking:

BAV19W: A8
BAV20W: T2
BAV21W: T3

**极限参数/Absolute maximum ratings(Ta=25°C)**

参数	符号	BAV19W	BAV20W	BAV21W	单位
Non-Repetitive Peak Reverse Voltage	V _{RM}	120	200	250	V
Peak Repetitive Peak Reverse Voltage	V _{RPM}	100	150	250	V
Working Peak Reverse Voltage	V _{RWM}	100	150	250	V
DC Blocking Voltage	V _R	100	150	250	V
RMS Reverse Voltage	V _{R(RMS)}	71	106	141	V
Forward Continuous Current	I _{FM}	400			mA
Average Rectified Output Current	I _o	200			mA
Peak Forward Surge Current	I _{FSM}	2.5 (@=1.0mS) 0.5 (@=1.0S)			A
Repetitive Peak Forward Current	I _{FRM}	625			mA
Power Dissipation	P _D	0.5			W
Thermal Resistance Junction to Ambient Air	R _{θ JA}	250			°C/W
Storage Temperature	T _{stg}	-55~150			°C

电性能参数/Electrical characteristics (Ta=25°C)

参数/Parameter	符号	测试条件	最大值	单位
正向电压/Forward Voltage	V _{F1}	I _F =100mA	1.0	V
	V _{F2}	I _F =200mA	1.25	V
反向漏电流/Reverse Current BAV19W BAV20W BAV21W	I _R	V _R =100V	0.1	μA
		V _R =150V	0.1	μA
		V _R =200V	0.1	μA
端电容/Capacitance Between Terminals	C _T	V _R =0, f=1MHz	5	pF
反向恢复时间/Reverse Recovery Time	t _{rr}	I _F =I _R =30mA, I _{rr} =0.1 × I _R , R _L =100 Ω	50	nS